

## Standard Rectifier Module

<b>3~ Rectifier</b>	
$V_{RRM}$	= 1800 V
$I_{DAV}$	= 90 A
$I_{FSM}$	= 750 A

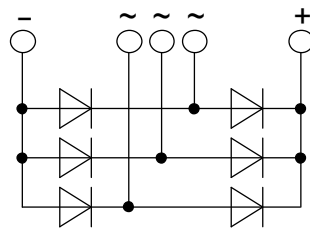
### 3~ Rectifier Bridge

Part number

VUO82-18N07



 E72873



#### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

#### Applications:

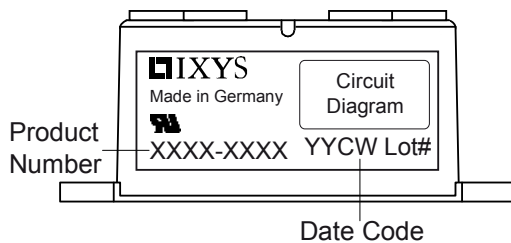
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

#### Package: PWS-D

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1900	V	
$V_{RRM}$	max. repetitive reverse blocking voltage					1800	V	
$I_R$	reverse current	$V_R = 1800$ V	$T_{VJ} = 25^\circ\text{C}$			100	$\mu\text{A}$	
		$V_R = 1800$ V	$T_{VJ} = 150^\circ\text{C}$			1.5	mA	
$V_F$	forward voltage drop	$I_F = 30$ A	$T_{VJ} = 25^\circ\text{C}$			1.08	V	
						1.35	V	
		$I_F = 90$ A	$T_{VJ} = 125^\circ\text{C}$			0.99	V	
						1.33	V	
$I_{DAV}$	bridge output current	$T_C = 115^\circ\text{C}$ rectangular	$T_{VJ} = 150^\circ\text{C}$			90	A	
								$d = \frac{1}{3}$
$V_{FO}$	threshold voltage					0.78	V	
$r_F$	slope resistance					6	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case					0.9	K/W	
$R_{thCH}$	thermal resistance case to heatsink				0.4		K/W	
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		135	W	
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			750	A	
								$t = 8,3$ ms; (60 Hz), sine
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$				640	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			2.82	kA <sup>2</sup> s	
								$t = 8,3$ ms; (60 Hz), sine
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$				2.05	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		27	pF	

Package PWS-D			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			150	A
$T_{stg}$	storage temperature		-40		125	°C
$T_{VJ}$	virtual junction temperature		-40		150	°C
<b>Weight</b>				159		g
$M_D$	mounting torque		4.25		5.75	Nm
$M_T$	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	9.5			mm
$d_{Spb/Appb}$		terminal to backside	26.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO82-18NO7	VUO82-18NO7	Box	10	502555

### Equivalent Circuits for Simulation

\* on die level

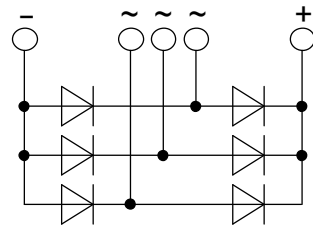
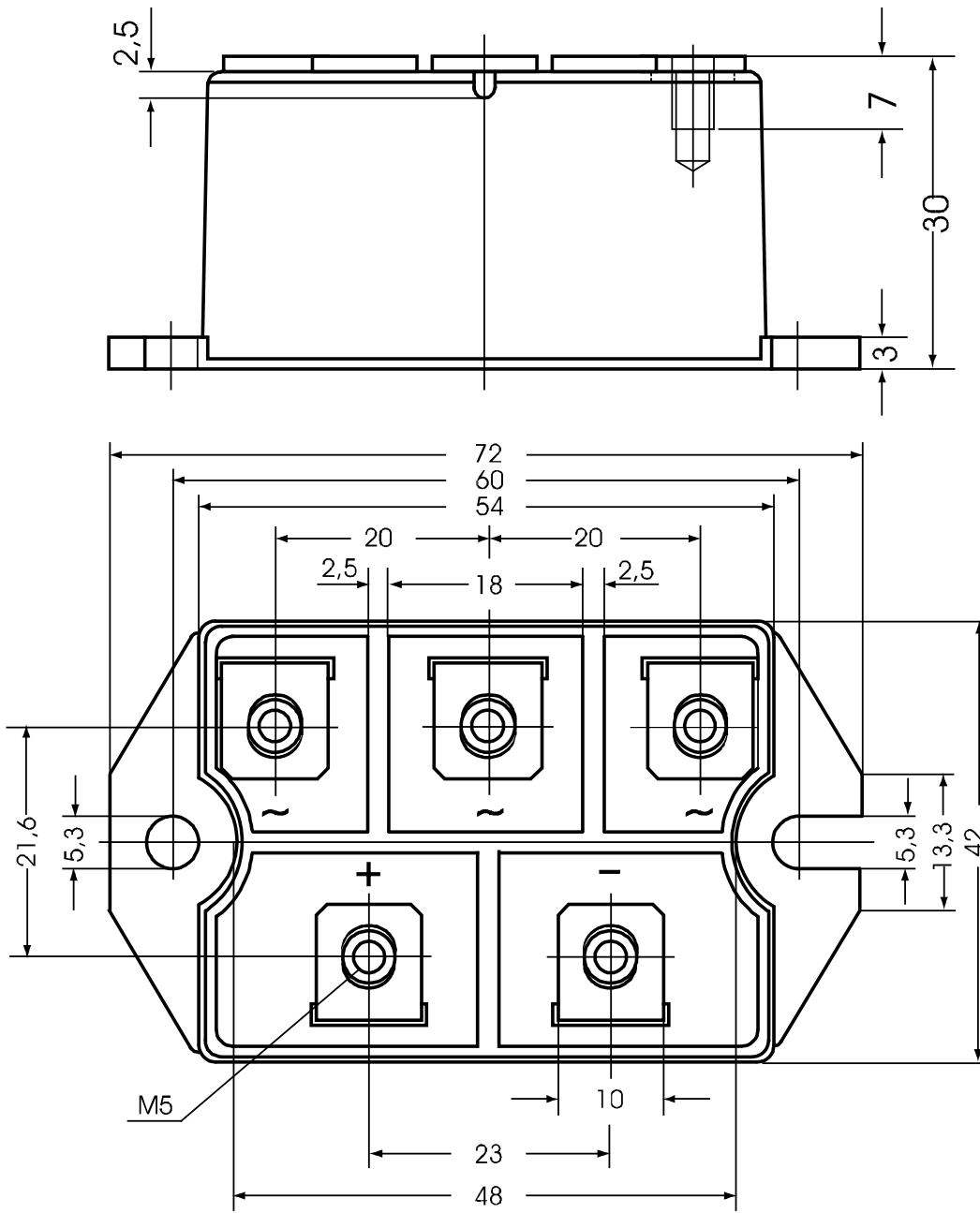
$T_{VJ} = 150\text{ °C}$



Rectifier

$V_{0\ max}$	threshold voltage	0.78	V
$R_{0\ max}$	slope resistance *	4.8	mΩ

## Outlines PWS-D



## Rectifier

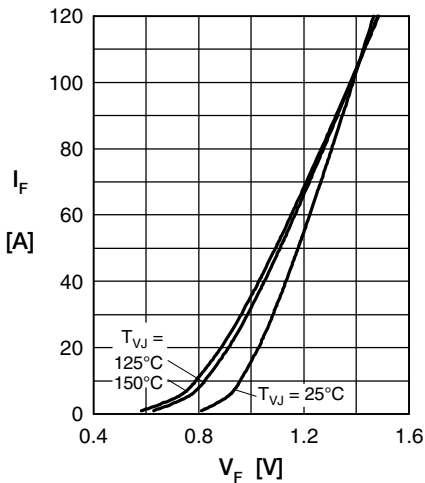


Fig. 1 Forward current versus voltage drop per diode

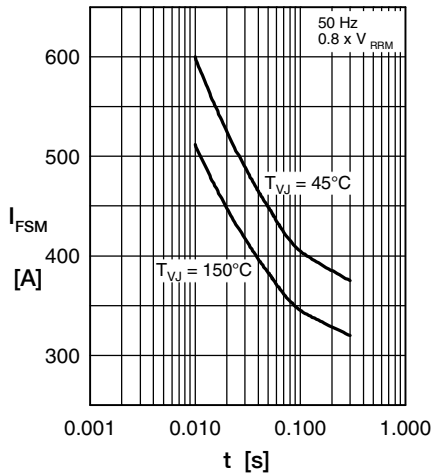


Fig. 2 Surge overload current

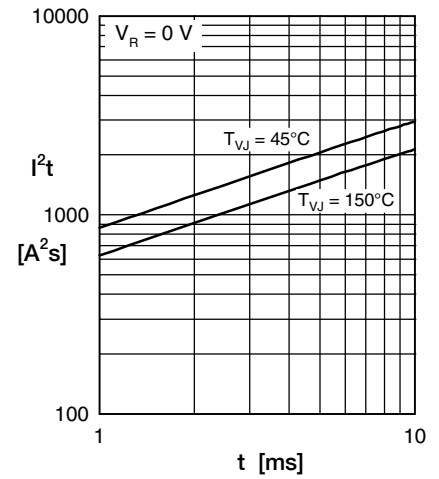


Fig. 3  $I^2t$  versus time per diode

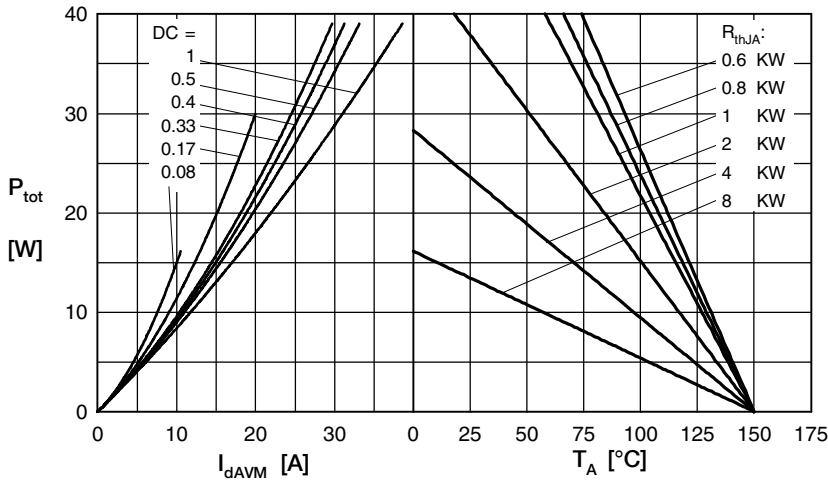


Fig. 4 Power dissipation vs. direct output current & ambient temperature

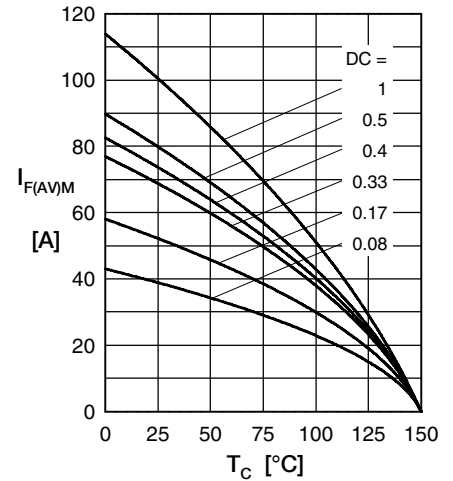


Fig. 5 Max. forward current vs. case temperature

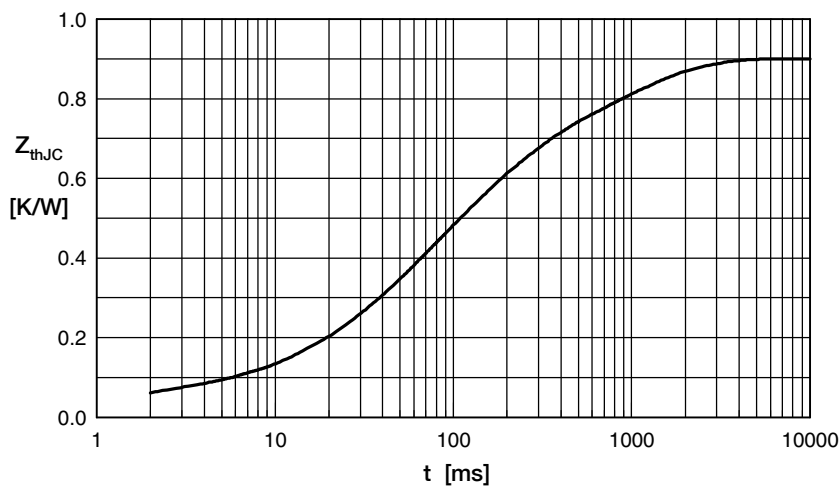


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.05	0.001
2	0.14	0.030
3	0.18	0.070
4	0.28	0.150
5	0.25	0.950